Electronic Supplementary Information

Fabrication and photoelectrochemical characteristics of CuInS$_2$ and PbS quantum dots co-sensitized TiO$_2$ nanorods photoelectrodes

Minmin Han$^{a,b}$, Junhong Jia$^a$*, Limin Yu$^{a,b}$, Gewen Yi$^a$

$^a$ State Key Laboratory of Solid Lubrication, Lanzhou Institute of Chemical Physics, Chinese Academy of Sciences, Lanzhou, 730000, P. R. China.
$^b$ University of Chinese Academy of Sciences, Beijing, 100080, P. R. China.

* Corresponding author. Tel./Fax: +86-931-4968611.
E-mail address: jhjia@licp.cas.cn (J. Jia)
Fig. S1 TEM images of (a) CuInS$_2$(4)/TiO$_2$, (b) CuInS$_2$(8)/TiO$_2$, (c) PbS(2)/CuInS$_2$(6)/TiO$_2$, (d) PbS(6)/CuInS$_2$(6)/TiO$_2$.

Fig. S1a shows the TEM image of CuInS$_2$(4)/TiO$_2$. It can be seen that there are a small quantity of QDs on the surface of TiO$_2$ nanorod. After 8 depositing cycles, there are a large number of QDs covered over the surface of TiO$_2$ nanorod (Fig. S1b). When the PbS QDs are deposited on the TiO$_2$ nanorod arrays by 2 cycles, the surface of TiO$_2$ nanorod becomes rougher than that without PbS QDs (Fig. S1c). The QDs aggregate into some large bulk QDs with size out of the quantum size range seriously in the PbS(6)/CuInS$_2$(6)/TiO$_2$ photoelectrode (Fig. S1d). The aggregation of excessive QDs weakens or even dissolves the quantum size effect, and increases the series resistance of photovoltaic devices, which decreases the photoelectrochemical performance of QDSSCs eventually.
In order to confirm the composition in PbS(4)/CuInS$_2$(6)/TiO$_2$ and valence states of elements, the XPS analysis of PbS(4)/CuInS$_2$(6)/TiO$_2$ is conducted as shown in Fig. S2. The survey spectrum shows the presence of Cu, In, Pb, S, Ti and O elements in the sample (Fig. S2a), and confirms the high purity of the PbS QDs, CuInS$_2$ QDs and TiO$_2$ nanorods (the carbon content and the C 1s line shape are typical of surface contamination detected in air-exposed oxide surfaces). High-resolution XPS spectrum
of the most intense peaks of the six main elements (Cu 2p\textsubscript{3/2}, In 3d\textsubscript{5/2}, Pb 4f\textsubscript{7/2}, S 2p, Ti 2p\textsubscript{3/2} and O 1s) are shown in Fig. S2b-g. As shown in Fig. S2b, the binding energies of 931.9 eV (Cu 2p\textsubscript{3/2}) and 951.8 eV (Cu 2p\textsubscript{1/2}) are consistent with Cu (I). The binding energy of Cu 2p\textsubscript{3/2} for Cu (II) usually centered at 942 eV,' does not appear, which can be concluded that only Cu (I) exists in the sample and Cu (II) of the raw material has been reduced during the preparing process. The binding energies of In 3d are 444.5 eV (In 3d\textsubscript{5/2}) and 452.08 eV (In 3d\textsubscript{3/2}), suggesting the presence of In (III) (Figure S2c). The peaks of the binding energies of 138.6 eV (Pb 4f\textsubscript{7/2}) and 143.5 eV (Pb 4f\textsubscript{5/2}) are assigned to Pb in PbS (Fig. S2d). The close up survey in S 2p region (161.8 eV) doublet peaks located at 161.38 eV (S 2p\textsubscript{3/2}) and 162.5 eV (S 2p\textsubscript{1/2}) with an energy difference of 1 eV (Fig. S2e), which are assigned to S coordinated to Cu, In and Pb.\textsuperscript{2} Moreover, the peaks of the binding energies at 458.7 eV and 464.6 eV were assigned to Ti 2p\textsubscript{3/2} and Ti 2p\textsubscript{1/2} (Fig. S2f), which are attributed to that of crystalline rutile TiO\textsubscript{2}, and the binding energy of the O 1s peak displayed in Fig. S2g at about 532.1 eV corresponds to that of O in TiO\textsubscript{2}.\textsuperscript{3}

Fig. S3 EDS line scan profiles of PbS(4)/CuInS\textsubscript{2}(6)/TiO\textsubscript{2} for Ti, O (a) and S, Cu, In, Pb (b) elementals. The inset in b is the STEM images.
To elucidate the structures of the PbS\((m)/CuInS_2(n)/TiO_2\) photoelectrodes, the energy dispersive spectroscopy (EDS) line scan in the scanning transmission electron microscope (STEM) is utilized. Fig. S3 shows the EDS line scan profiles of PbS(4)/CuInS\(_2\)(6)/TiO\(_2\) for Ti, O (a) and S, Cu, In, Pb (b) elementals, which reveals the relative locations of the embedded CuInS\(_2\) QDs and PbS QDs. There is a O-rich area in the middle of the samples (Fig. S3a) and the outer shell is the S-rich QD-layer (Fig. S3b). More importantly, the outermost shell of the QD-layer is Pb-rich and the inner layer is Cu-rich with a very clear line drawn in 30 nm and 170nm, manifesting the cascade structure of PbS(4)/CuInS\(_2\)(6)/TiO\(_2\) photoelectrode as described in Fig. 1f.

Fig. S4 Plots of \((αhv)^2\) against photon energy \((hv)\) for (a) CuInS\(_2\)(6)/TiO\(_2\) and (b) PbS(4)/TiO\(_2\) photoelectrodes.

Fig. S4 presents the plots of \((αhv)^2\) against photon energy \((hv)\) for CuInS\(_2\)(6)/TiO\(_2\) and PbS(4)/TiO\(_2\) photoelectrodes. The band gap of CuInS\(_2\)(6)/TiO\(_2\) and PbS(4)/TiO\(_2\) electrodes is 1.52 eV and 0.74 eV respectively, which is smaller than that of CuInS\(_2\) and PbS QDs but larger than that of bulk CuInS\(_2\) and PbS. Therefore, it can be determined that the enhanced absorption in the longer wavelength region is
due to the quantum confinement effect of the CuInS$_2$ and PbS QDs.

Fig. S5 EIS Nynquist plots of various photoelectrodes measured in the dark and under visible light irradiation. The EIS plot of TiO$_2$ nanorods is almost a straight line because of its property of non-response within visible light. After the deposition of CuInS$_2$ QDs, the curve radius reduces, which indicates that CuInS$_2$/TiO$_2$ electrode could greatly and effectively improve the separation of photo-generated electron–hole pairs. Meanwhile, the deposition of PbS QDs decrease the curve radius compared with CuInS$_2$/TiO$_2$ electrode, confirming the quicker interfacial charge transfer and electron injection process.
Fig. S6 Mott-Schottky plots of various photoelectrodes collected at a frequency of 5 kHz in the dark and under visible light irradiation.

To further elucidate the Fermi level alignment of PbS/CuInS$_2$/TiO$_2$ photoelectrodes and evaluate the electron-transfer properties of semiconductor interface, Mott-Schottky plots are measured in the dark and under visible light irradiation. The slope of Mott-Schottky plot represents the charge carrier density $N_D$ as it can be calculated by the equation: $N_D = (2/e_0\varepsilon \varepsilon_0)[d(1/C^2)/dV]^{-1}$, where $e_0$ is the elementary electron charge, $\varepsilon$ is the permittivity of the semiconductor electrode, $\varepsilon_0$ is the permittivity of vacuum and $d(1/C^2)/dV$ is the slope of Mott-Schottky plot, which means the smaller the slope of Mott–Schottky plot is, the higher the charge carrier density will be.$^4$ Thus, as we can see from Fig. S6, the charge carrier density of photoelectrode increases with the deposition of CuInS$_2$ and PbS QDs, which could lead to the upwards shift of the Fermi level, and the conduction band of CuInS$_2$ and
PbS QDs is enhanced relatively. Moreover, according to the literatures,\textsuperscript{5,6} the enlarged band gap of QDs could enhance the conduction band of semiconductor QDs, which lead to the expected higher conduction band of PbS QDs coupled with the upwards shift of the Fermi level as shown in Fig. 9b.

![EDX spectrum of CuInS\textsubscript{2}(6)/TiO\textsubscript{2}](image)

**Fig. S7** EDX spectrum of CuInS\textsubscript{2}(6)/TiO\textsubscript{2}.

To determine the element ratio of Cu: In: S of CuInS\textsubscript{2}, the energy dispersive X-Ray (EDX) spectroscopy is conducted on the sample of CuInS\textsubscript{2}(6)/TiO\textsubscript{2} and presented in Fig. S7. The atomic ratio of Cu: In: S is around 1: 1: 2, which matches with the stoichiometry of CuInS\textsubscript{2}. In addition, the atomic ratio of Ti: O is around 1: 2, corresponding to the stoichiometry of TiO\textsubscript{2}. The C element in the spectrum may be due to the carbon layer on the nickel grid. Hence, it can be conclude that the high stoichiometric CuInS\textsubscript{2} QDs are deposited on the surface of TiO\textsubscript{2} nanorods.

Fig. S8 shows the time stability of the unencapsulated QDSSC assembled with PbS(4)/CuInS\textsubscript{2}(6)/TiO\textsubscript{2} electrode. After two days, there is a slight relative decrease of
7% under ambient air. However, the normalized $\eta$ decreases by 30% after four days, which is maybe due to the instability and difficult attachment to TiO$_2$ nanorods of QDs. The stability of QDSSCs is relatively poor and need further investigation.

Fig. S8 Time stability, under ambient air, of the normalized current density ($J_{SC}$) of QDSSC assembled with PbS(4)/CuInS$_2$(6)/TiO$_2$ electrode.

REFERENCES


